

Supporting information

3D hierarchical $\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ nanoarrays as cathode materials for asymmetric pseudocapacitor

Bo Liu,^{‡a} Dezhi Kong,^{‡a,b} Ye Wang,^a Jun Zhang,^c Tupei Chen,^c Chuanwei Cheng,^b and Hui Ying Yang^{a,*}

^a Pillar of Engineering Product Development, Singapore University of Technology and Design, 8 Somapah Road, Singapore, 487372

^b Shanghai Key Laboratory of Special Artificial Microstructure Materials and Technology, School of Physics Science and Engineering, Tongji University, Shanghai 200092, P. R. China

^c School of Electrical and Electronic Engineering, Nanyang Technological University, Singapore 639798, Singapore

[‡] These authors contribute equally to this work.

*Corresponding author. Tel.: +65 6303 6663; Fax: +65 6779 5161. E-mail address: yanghuiying@sutd.edu.sg (H. Y. Yang)

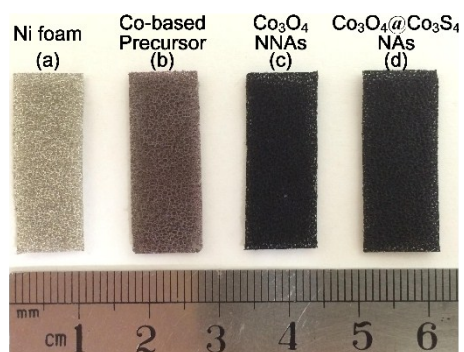


Figure S1 Optical photograph of Ni foam substrate (a), Co-based precursor on Ni foam (b), Co₃O₄ NNAs on Ni foam (c), and Co₃O₄@Co₃S₄ NNAs on Ni foam (d).

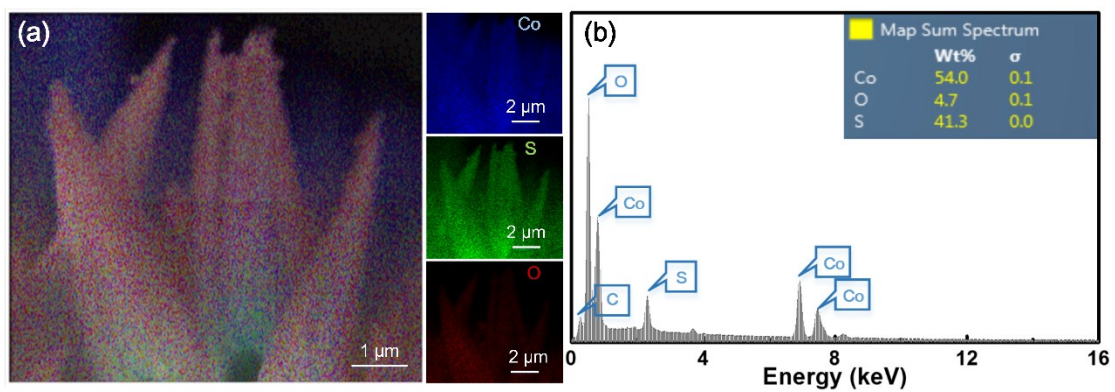


Figure S2 (a) SEM image of the $\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ nanostructure and EDS elemental maps of Co, S, and O; (b) EDS elemental spectrum of hybrid NAs.

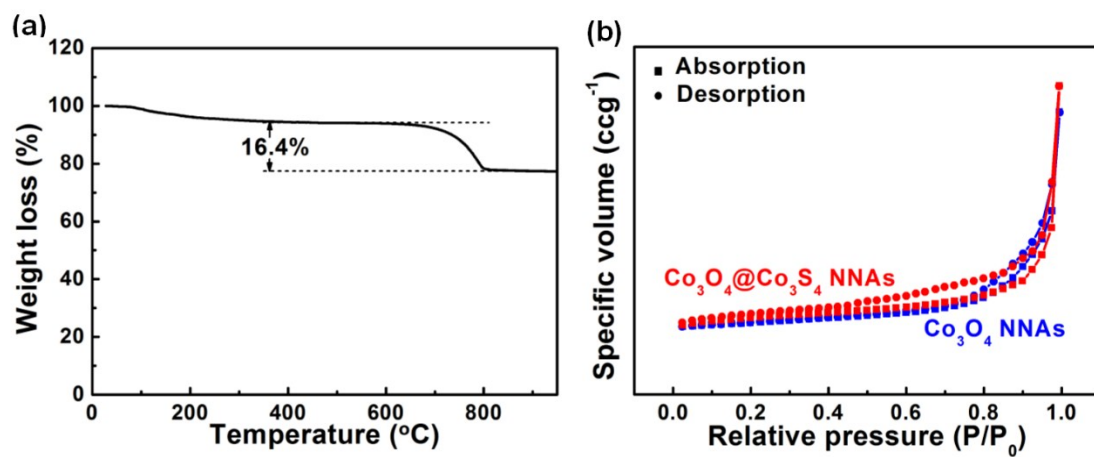


Figure S3 (a) The TGA profile of the Co₃O₄@Co₃S₄ NNAs; (b) Adsorption-desorption isotherms of the Co₃O₄ NNAs and Co₃O₄@Co₃S₄ NNAs.

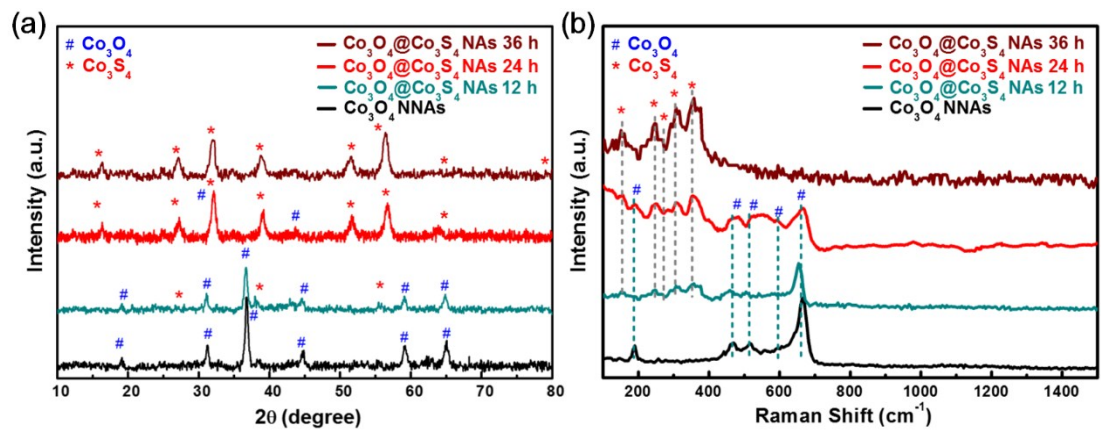


Figure S4 (a) XRD patterns and (b) Raman spectra of Co_3O_4 NNAs, $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4$ NAs 12h, $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4$ NAs 24h, and $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4$ NAs 36h.

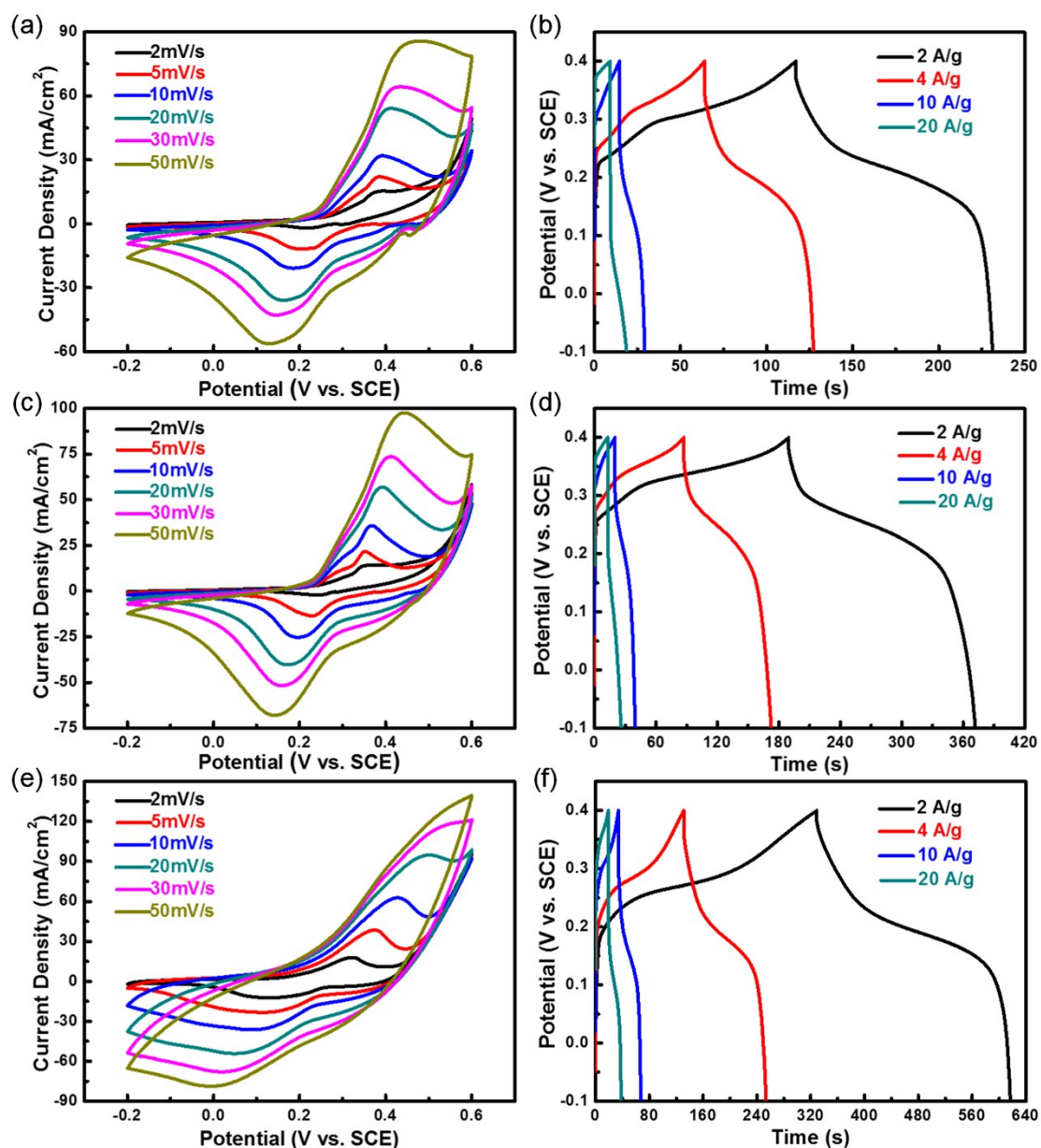


Figure S5 (a) CV and (b) galvanostatic charge-discharge curves of the Co₃O₄ NNAs electrode; (c) CV and (d) galvanostatic charge-discharge curves of Co₃O₄@Co₃S₄ NAs prepared at 12 h in the second hydrothermal synthesis process; (e) CV and (d) galvanostatic charge-discharge curves of Co₃O₄@Co₃S₄ NAs prepared at 36 h in the second hydrothermal synthesis process.

Table 1. Scan-Rate-Dependent Specific Capacitances (F/g) of the Co_3O_4 , $\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ 12 h, $\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ 24 h, and $\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ 36 h Electrodes

	scan rate (mV/s)					
	2	5	10	20	30	50
Co_3O_4	765.6	317.2	186.2	127.6	98.5	74.2
$\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ (12 h)	911.5	410.4	288.5	242.2	218.1	184.4
$\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ (24 h)	1284.3	631.9	425.1	311.1	283.7	206.7
$\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ (36 h)	1161.5	642.7	447.9	316.7	258.9	177.4

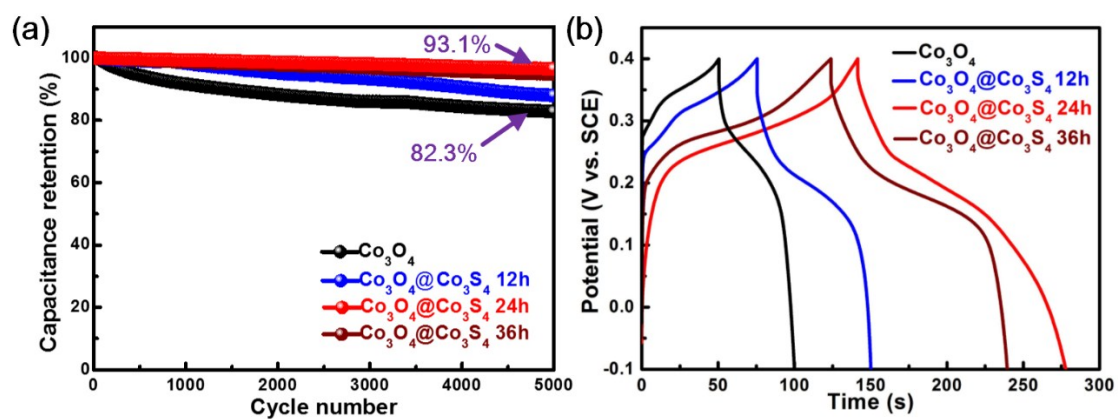


Figure S6 (a) Cycling performance of the Co_3O_4 NNAs and $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4$ NAs electrodes prepared at different reaction durations in the second hydrothermal synthesis process ; (b) Galvanostatic charging/discharging curves of the last cycle at 4 A g^{-1} after 5000 cycles for the Co_3O_4 NNAs and $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4$ NAs electrodes, respectively.

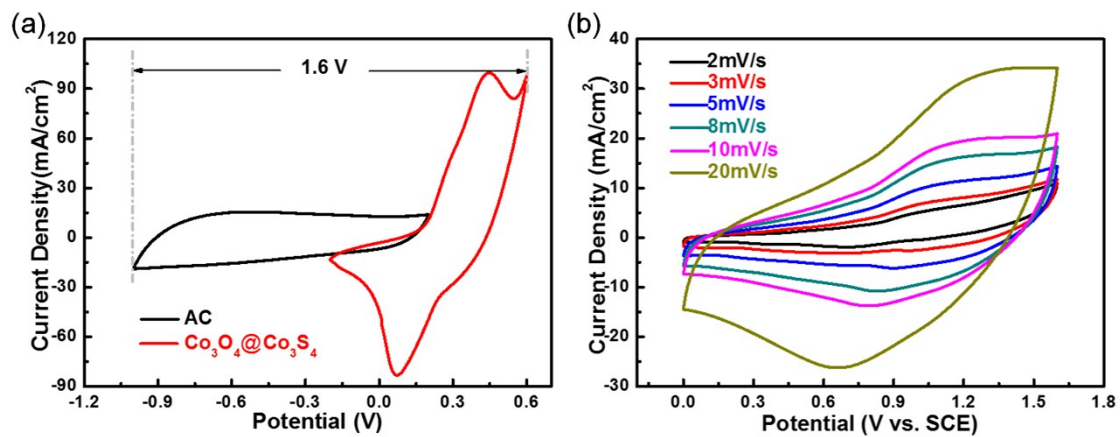


Figure S7 (a) The CV comparison of the activated carbon electrodes and the $\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4$ NAS electrodes in -0.2 to 0.6 V and -1.0 to 0.2 V at a scan rate of 30 mV s^{-1} ; (b) CV curves of the $\text{Co}_3\text{O}_4@\text{Co}_3\text{S}_4//\text{AC}$ ASCs at various scan rates.

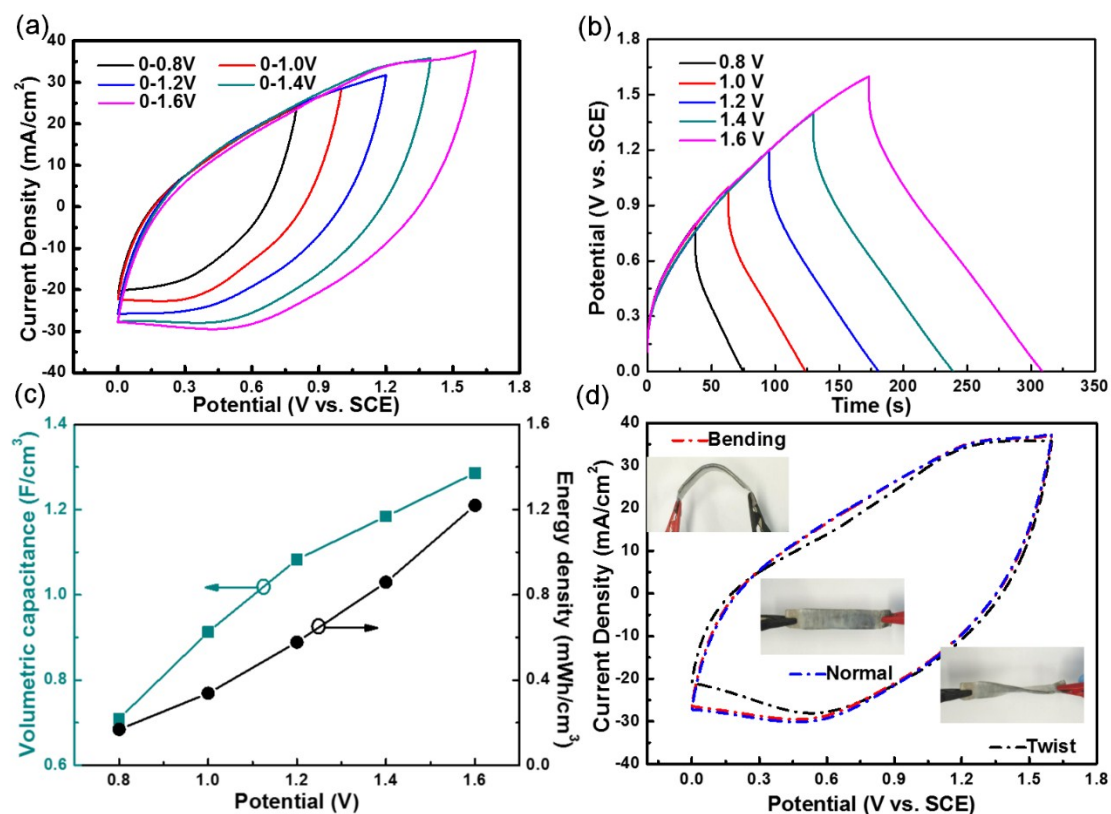


Figure S8 (a) CV curves of the $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4// \text{AC}$ ASCs measured at various potential windows with a scan rate of 20 mV s^{-1} ; (b) Galvanostatic discharge-charge curves collected at different potential windows for the $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4// \text{AC}$ ASCs (5 mA cm^{-2}); (c) Volumetric capacitance calculated from CV and discharge curves as a function of potential window for the $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4// \text{AC}$ ASCs; (d) CV curves collected at a scan rate of 20 mV s^{-1} for the $\text{Co}_3\text{O}_4@ \text{Co}_3\text{S}_4// \text{AC}$ ASCs under normal, bending, and twist conditions, and the insets of (d) are the device pictures under test conditions.